

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

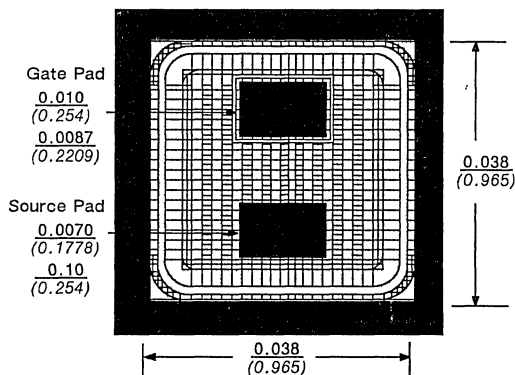
- Switching
- Amplification

FEATURES

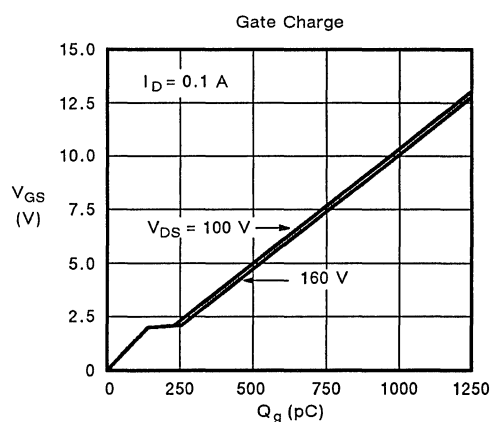
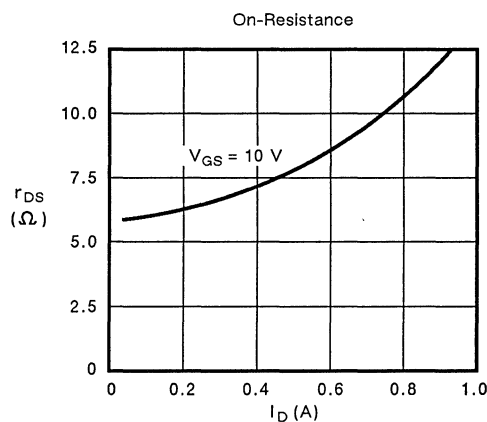
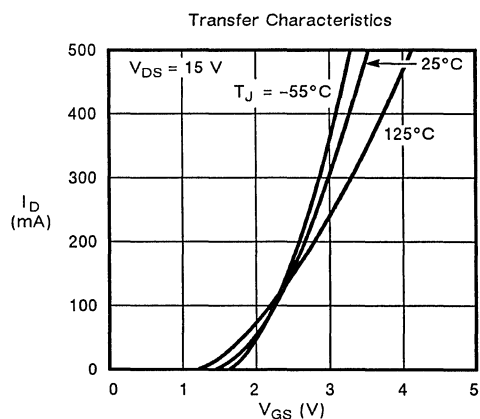
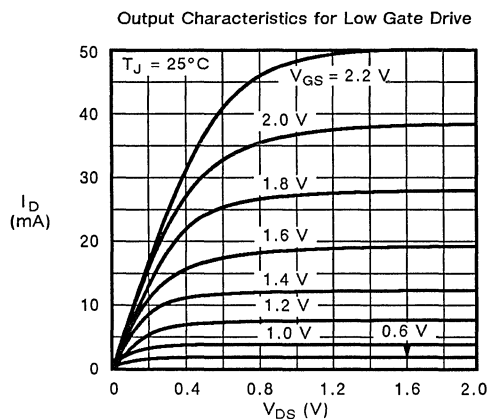
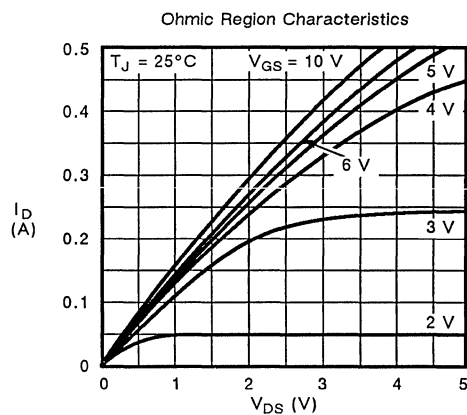
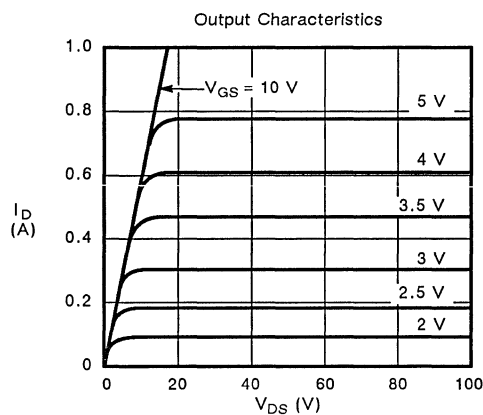
- High Breakdown > 200 V
- Low $r_{DS(on)} < 10 \Omega$

TYPE	PACKAGE	DEVICE
Single	TO-92	• BS107 • VN2010L, VN2020L
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

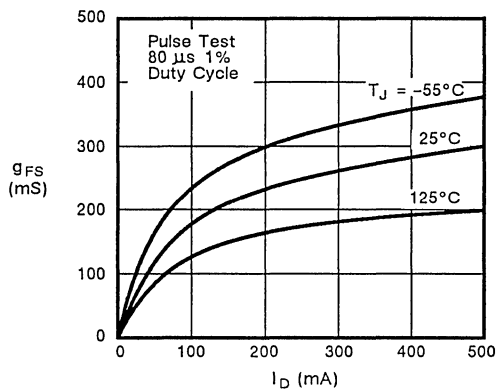


TYPICAL CHARACTERISTICS

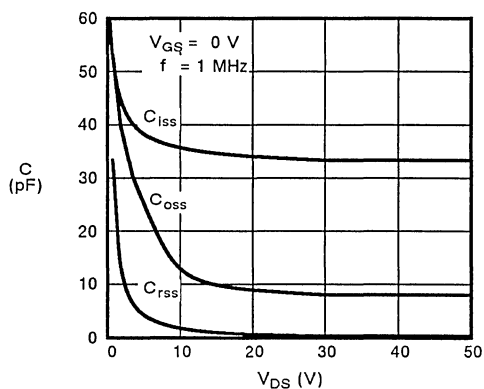


TYPICAL CHARACTERISTICS

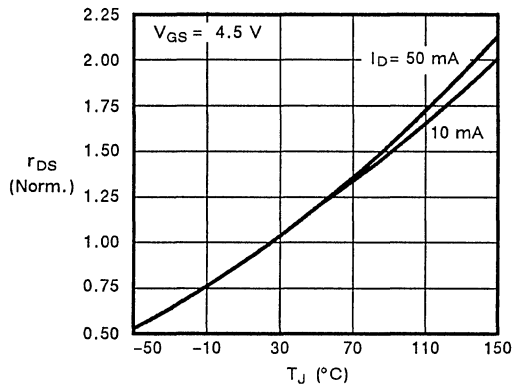
Transconductance



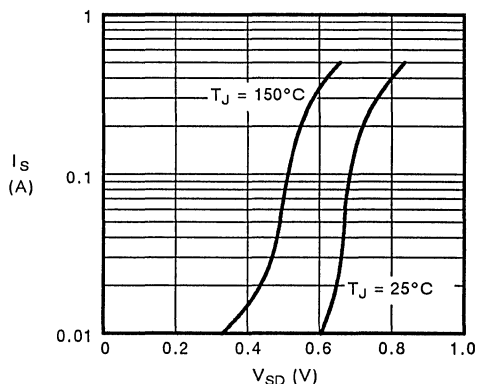
Capacitance



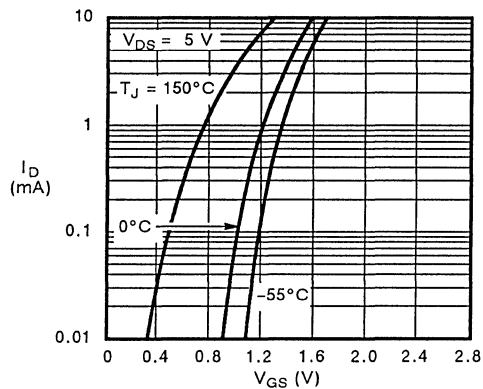
On-Resistance vs. Junction Temperature



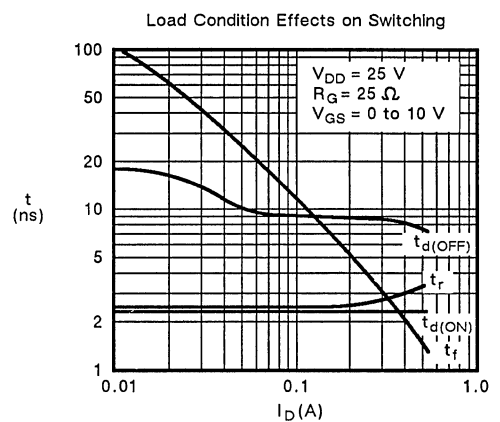
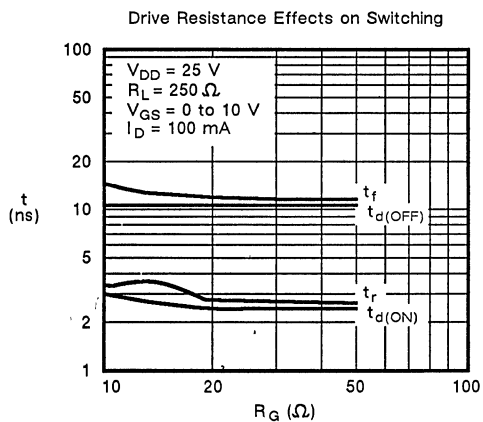
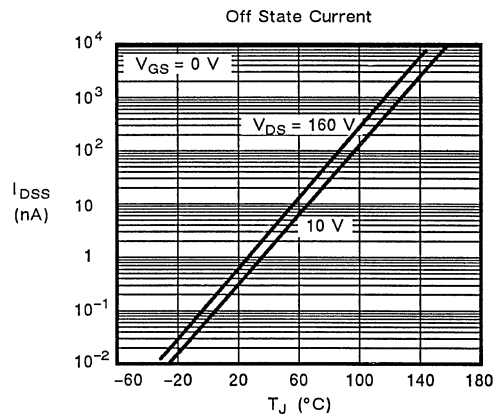
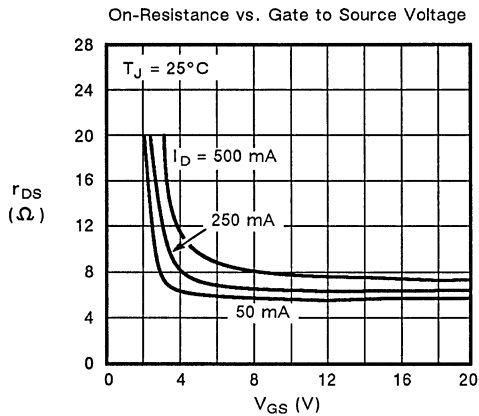
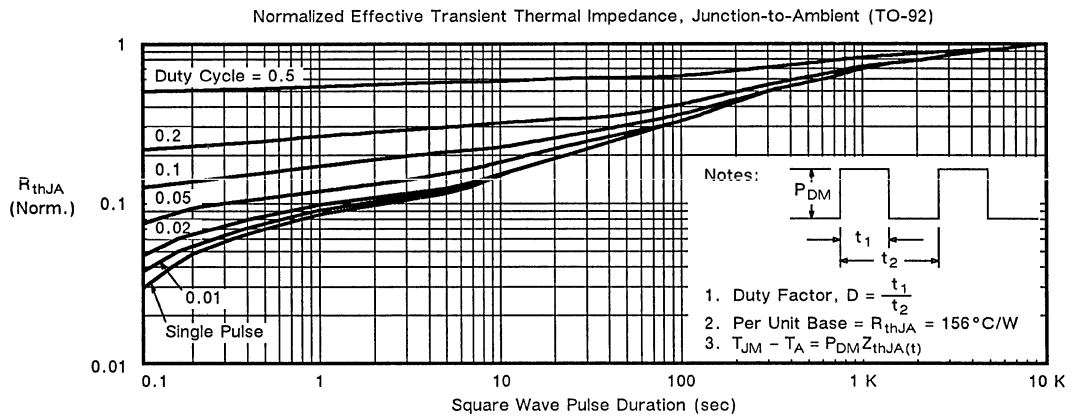
Source-Drain Diode Forward Voltage



Threshold Region

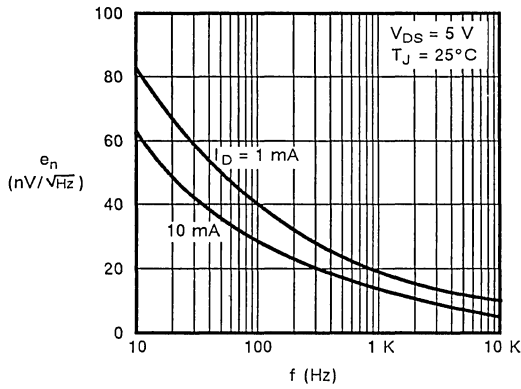


TYPICAL CHARACTERISTICS

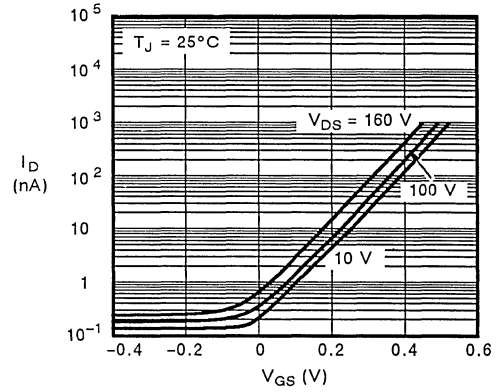


TYPICAL CHARACTERISTICS

Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current

